

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI TVV100 is Designed for

FEATURES:

- Input Matching Network
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	16 A
V_{CB0}	65 V
V_{CEO}	33 V
V_{EBO}	3.5 V
P_{DISS}	150 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.8 °C/W

PACKAGE STYLE .400 8L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.030 / 0.76	
B	.115 / 2.92	.125 / 3.18
C	.360 / 9.14	
D	.065 / 1.65	.075 / 1.91
E	.130 / 3.30	
F	.380 / 9.65	.390 / 9.91
G	.735 / 18.67	.765 / 19.43
H	.645 / 16.38	.655 / 16.64
I	.895 / 22.73	.905 / 22.99
J	.420 / 10.67	.430 / 10.92
K	.003 / 0.08	.007 / 0.18
L	.120 / 3.05	.130 / 3.30
M	.159 / 4.04	.175 / 4.45
N		.280 / 7.11
O	.395 / 10.03	.405 / 10.29

ORDER CODE: ASI10662

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 50 mA	65			V
BV_{CER}	I _C = 50 mA R _{BE} = 15 Ω	60			V
BV_{CEO}	I _C = 50 mA	33			V
BV_{EBO}	I _E = 5.0 mA	3.5			V
h_{FE}	V _{CE} = 5.0 V I _C = 500 mA	20		150	---
C_{OB}	V _{CB} = 28 V f = 1.0 MHz	---	60	---	pF
P_G	V _{CE} = 28 V I _C = 2 X 100 mA f = 225 MHz P _{OUT} = 100 W	11			dB